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- 16. The photoresist composition of claim 1 wherein the polymer is a tetrapolymer or a pentapolymer.
- 17. (amended) The photoresist composition of claim 1 wherein the polymer is substantially free of aromatic groups.
- 18. (amended) The photoresist composition of claim 1 wherein the photoactive component comprises one or more photoacid generator compounds.
- 19. (amended) The photoresist composition of claim 1 wherein the photoresist is a chemically-amplified positive-acting resist.
 - 20. (amended) A method of forming a positive photoresist relief image, omprising:
 - (a) applying a coating layer of a photoresist of claim 1 on a substrate; and
 - (b) exposing and developing the photoresist layer to yield a relief image.
- 24. (amended) An article of manufacture comprising a microelectronic wafer substrate or flat panel display substrate having coated thereon a layer of the photoresist composition of claim 1.

REMARKS

The specification has been amended to include the priority claim. For the sole purpose of reducing initial filing fees, claims 21-23 and 26-40 have been cancelled without prejudice, and claims 3, 4, 6, 7, 9-20 and 24 have been amended to eliminate multiple dependencies.

Early consideration and allowance of the application are solicited.

Respectfully submitted,

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VERSION WITH CHANGES MARKED

- 3. (amended) A photoresist composition of claim 1 [or 2] wherein the polymer comprises photoacid-labile groups.
- 4. (amended) A photoresist composition of <u>claim 1</u> [any one of claims 1 through 3] wherein polymer further comprises a carbon alicyclic group fused to the polymer backbone.
- 6. (amended) The photoresist composition of claim [4 or] 5 wherein the carbon alicyclic group comprises a photoacid-labile group.4
- 7. (amended) A photoresist composition of <u>claim 1</u> [any one of claims 1 through 6] wherein the polymer comprises a heteroalicyclic group in addition to the carbonate or lactone.
- 9. (amended) The photoresist composition of claim [7 or] 8 wherein the additional heteroalicyclic group has a non-hydrogen ring substituent.
- 10. (amended) The photoresist composition of <u>claim 1</u> [any one of claims 1 through 9] wherein the polymer comprises a photoacid-labile group that is a substituent of an additional heteroalicyclic polymer group or a carbon alicyclic polymer group.
- 11. (amended) The photoresist composition of <u>claim 1</u> [any one of claims 1 through 10] wherein the polymer comprises a photoacid-labile moiety of a polymer unit separate a carbonate, lactone or carbon alicyclic unit.
- 12. (amended) The photoresist composition of <u>claim 1</u> [any one of claims 1 through 11] wherein the polymer comprises a polymerized acrylate that comprises a photoacid-labile moiety.

- 13. (amended) The photoresist composition of <u>claim 1</u> [any one of claims 1 through 12] wherein the polymer further comprises anhydride units.
- 14. (amended) The photoresist composition of <u>claim 1</u> [any one of claims 1 through 13] wherein the polymer further comprises maleic anhydride units.
- 16. The photoresist composition of <u>claim 1</u> [any one of claims 1 through 14] wherein the polymer is a tetrapolymer or a pentapolymer.
- 17. (amended) The photoresist composition of <u>claim 1</u> [any one of claims 1 [through 16] wherein the polymer is substantially free of aromatic groups.
- 18. (amended) The photoresist composition of <u>claim 1</u> [any one of claims 1 through 17] wherein the photoactive component comprises one or more photoacid generator compounds.
 - 19. (amended) The photoresist composition of <u>claim 1</u> [any one of claims 1 through 18] wherein the photoresist is a chemically-amplified positive-acting resist.
 - 20. (amended) A method of forming a positive photoresist relief image, comprising:
 - (a) applying a coating layer of a photoresist of <u>claim 1</u> [any one of claims 1 though 19] on a substrate; and
 - (b) exposing and developing the photoresist layer to yield a relief image.

24. (amended) An article of manufacture comprising a microelectronic wafer substrate or flat panel display substrate having coated thereon a layer of the photoresist composition of <u>claim 1</u> [any one of claims 1 though 19].

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